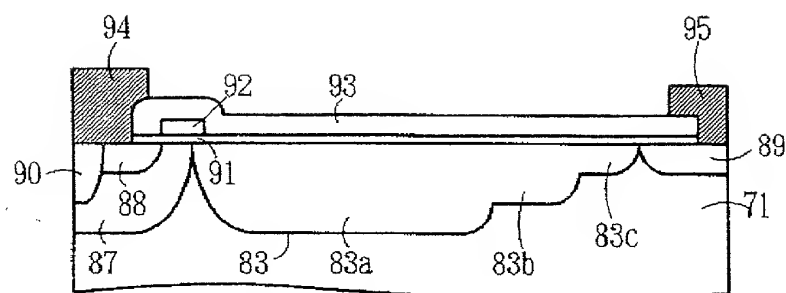


Fig. 1



- |                               |   |
|-------------------------------|---|
| 71: n-type silicon substrate  | 89: n-type drain region                 |
| 83: p-type offset region      | 90: p <sup>+</sup> -type contact region |
| 83a: First p-type sub-region  | 91: Gate insulation film                |
| 83b: Second p-type sub-region | 92: Gate electrode                      |
| 83c: Third p-type sub-region  | 93: Insulation film                     |
| 87: p-type base region        | 94: Source electrode                    |
| 88: n-type source region      | 95: Drain electrode                     |

Fig. 2

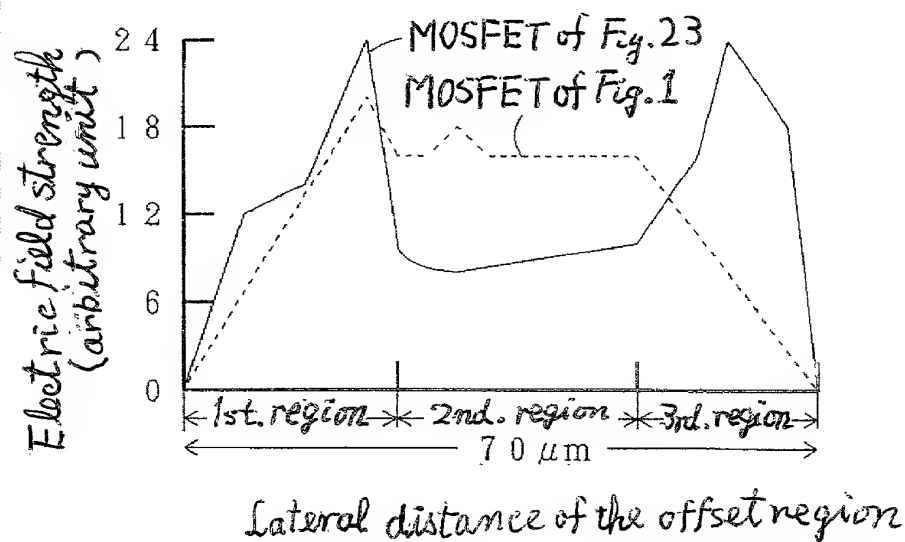


Fig. 3

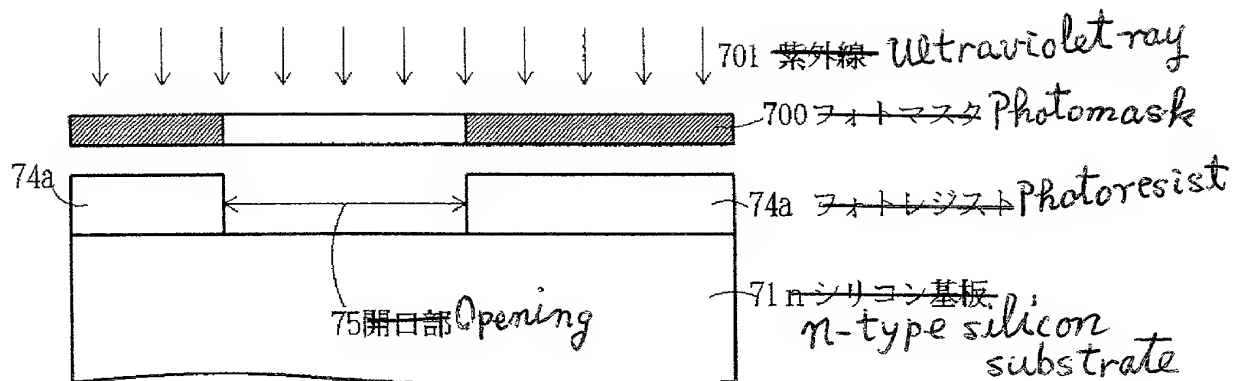


Fig. 4

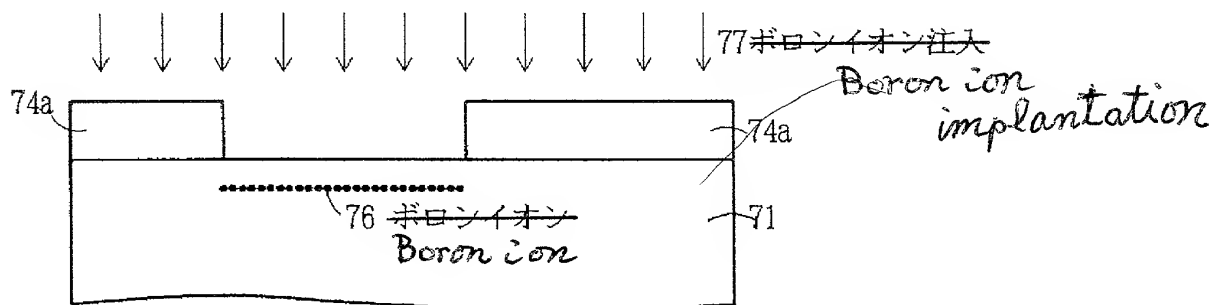


Fig. 5

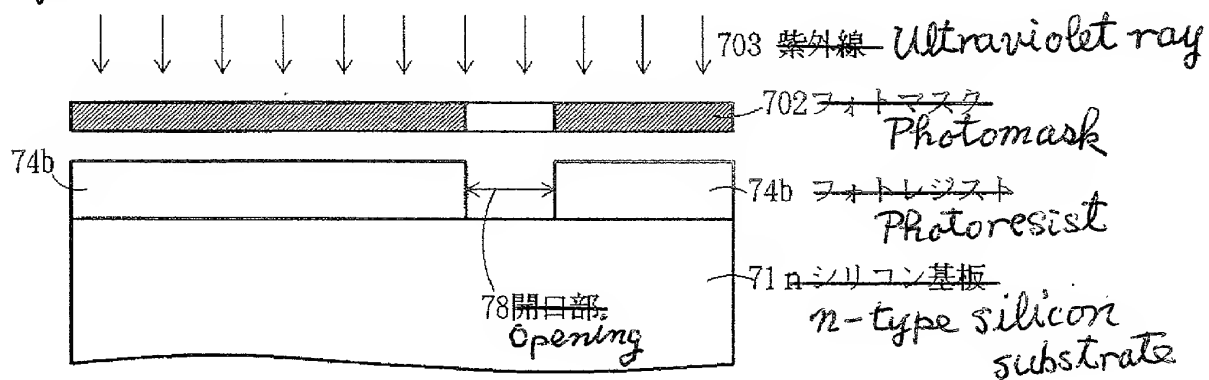


Fig. 6

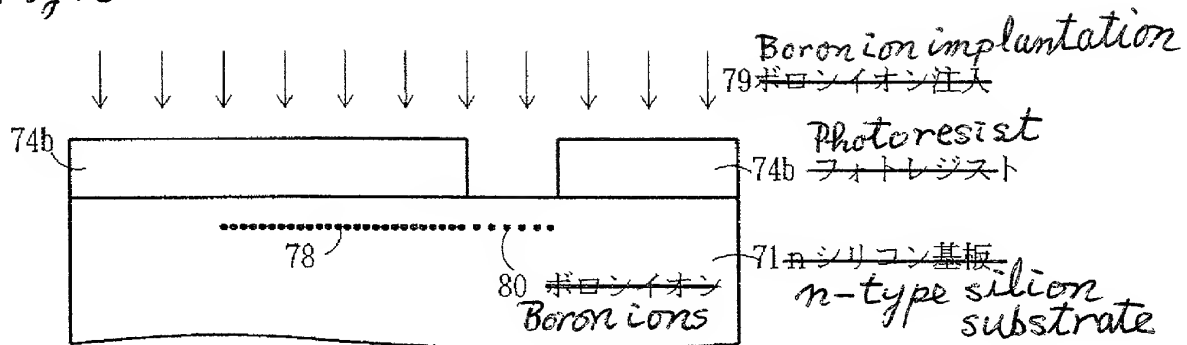


Fig. 7

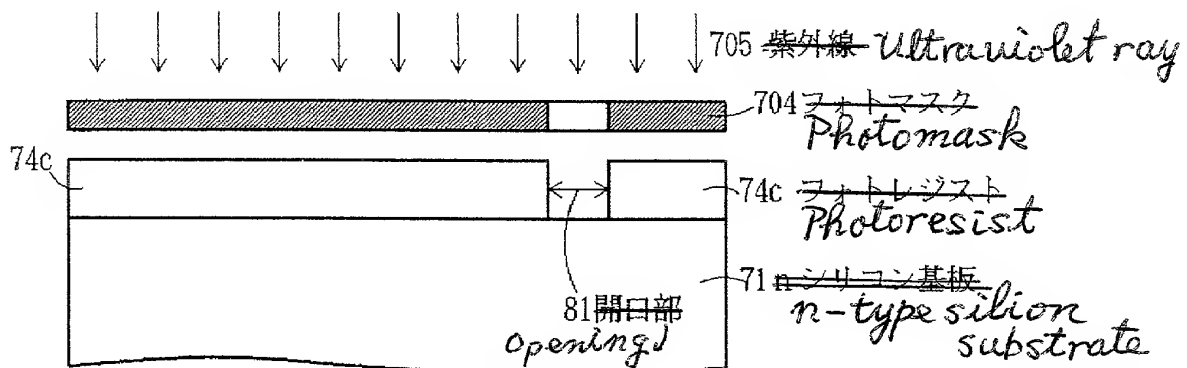


Fig. 8

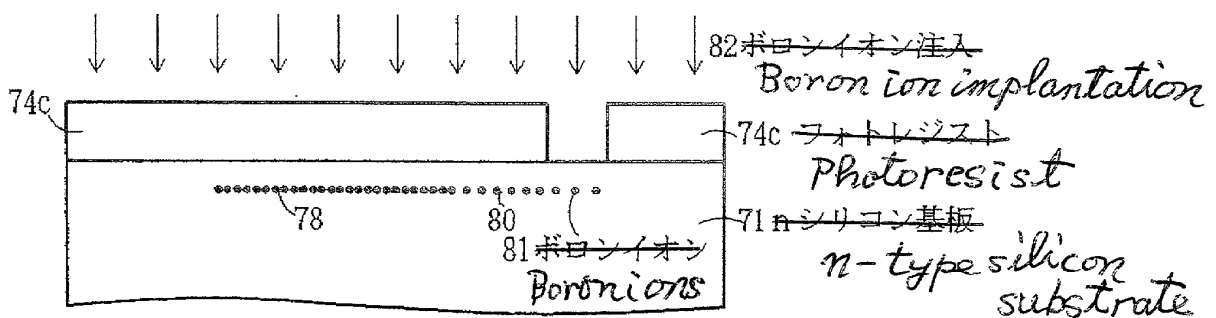


Fig. 9

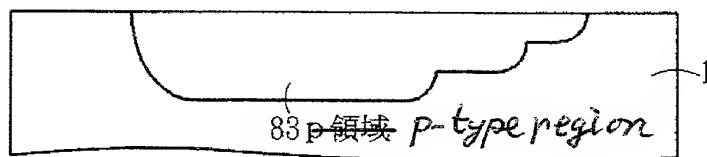


Fig. 10

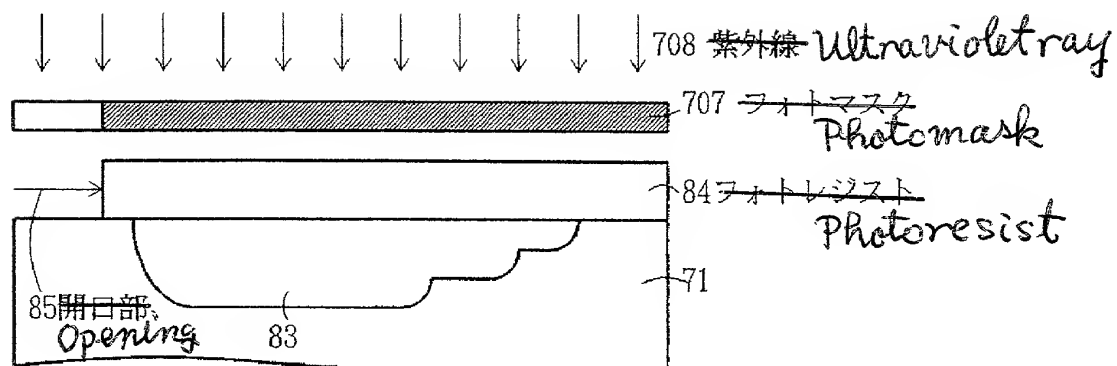


Fig. 11

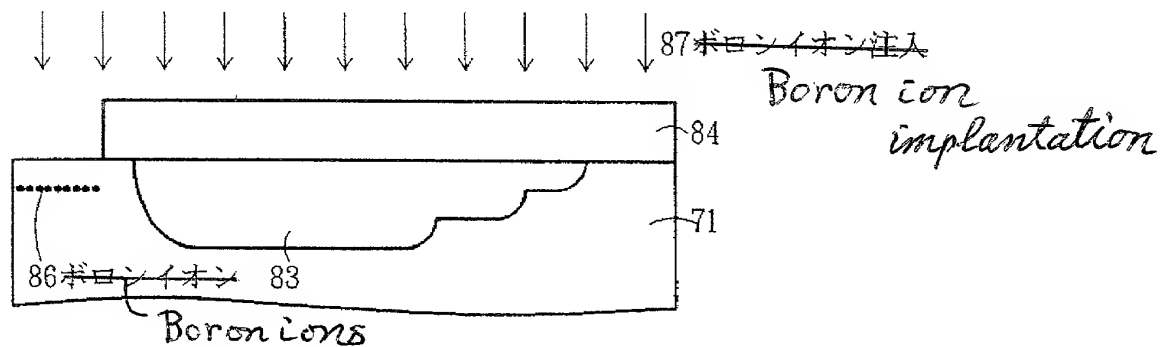


Fig. 12

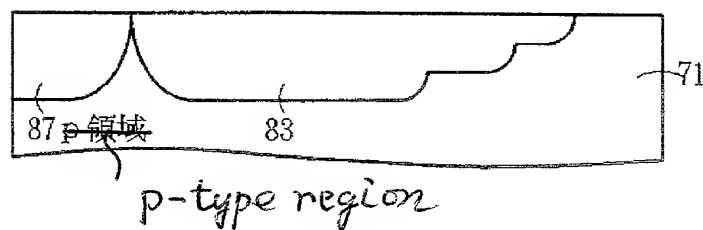
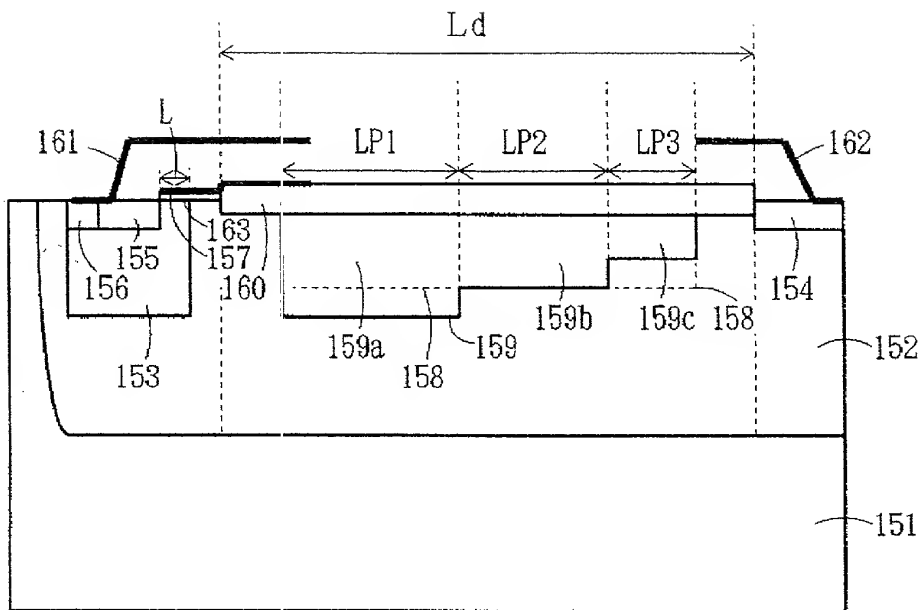


Fig. 13



- 151: p-type substrate
- 152: n-type well region
- 153: p-type base region
- 154: n-type drain region
- 155: n-type source region
- 156: p<sup>+</sup>-type contact region
- 157: Gate electrode
- 158: Boron diffusion depth
- 159: p-type diffusion region (p-type offset region)
- 159a: First p-type sub-region
- 159b: Second p-type sub-region
- 159c: Third p-type sub-region
- 160: Insulation film
- 161: Source electrode
- 162: Drain electrode
- 163: Gate insulation film

Fig. 14

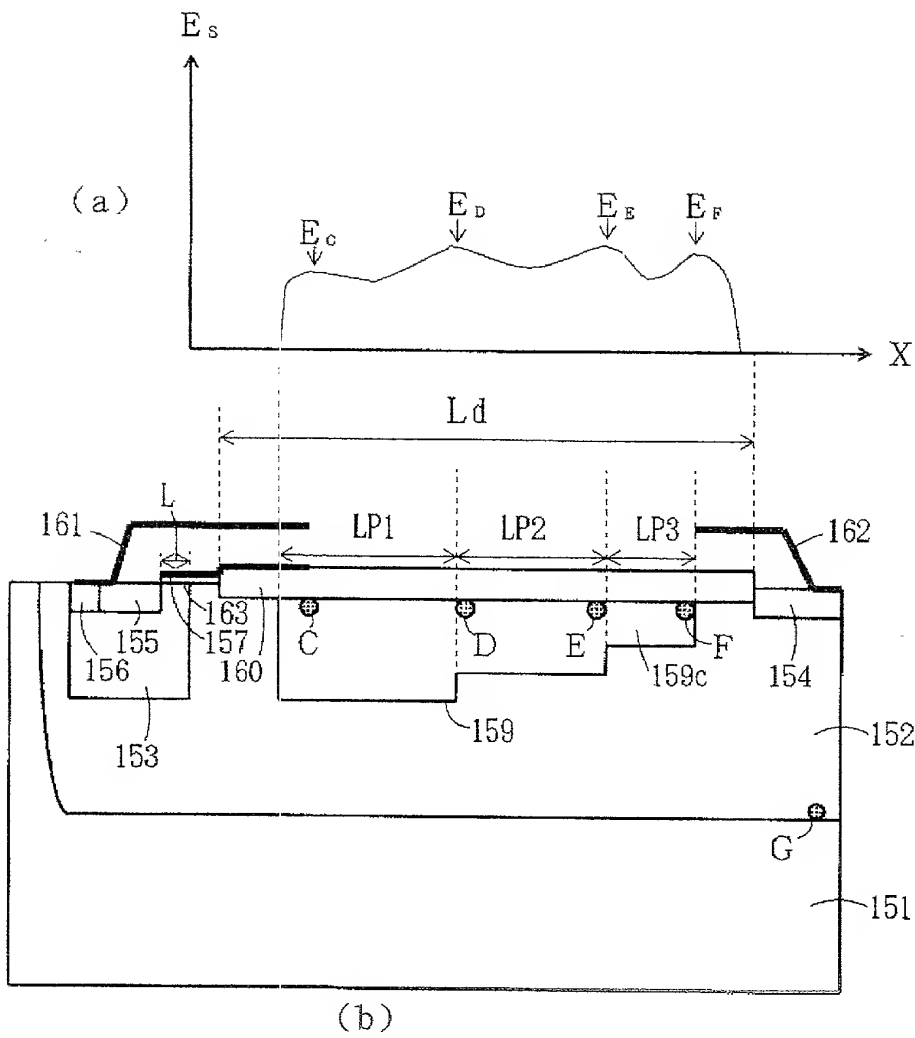
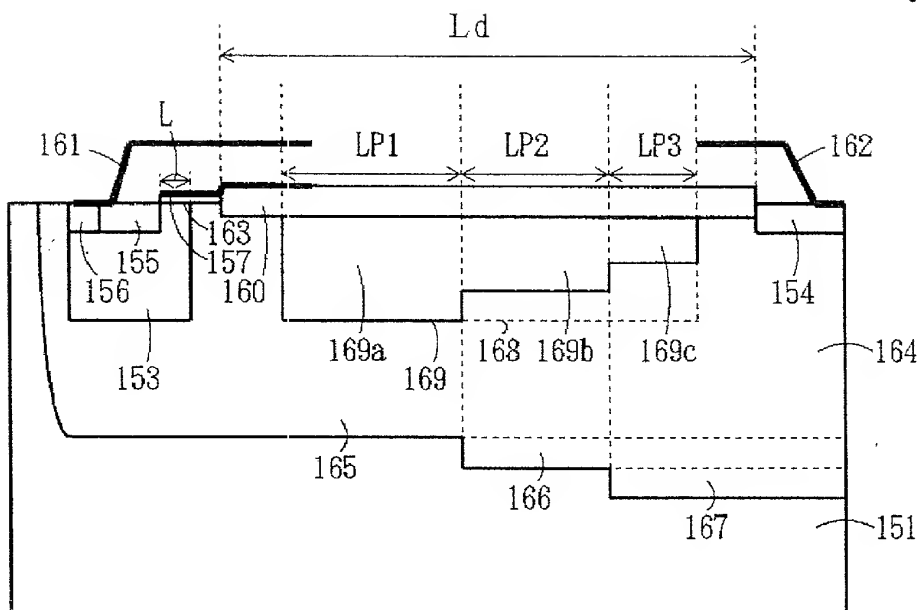


Fig. 15



- 164: n-type well region  
165: First well sub-region  
166: Second well sub-region  
167: Third well sub-region  
168: Boron diffusion depth  
169: p-type diffusion region  
169a: First p-type sub-region  
169b: Second p-type sub-region  
169c: Third p-type sub-region

Fig. 16(a)

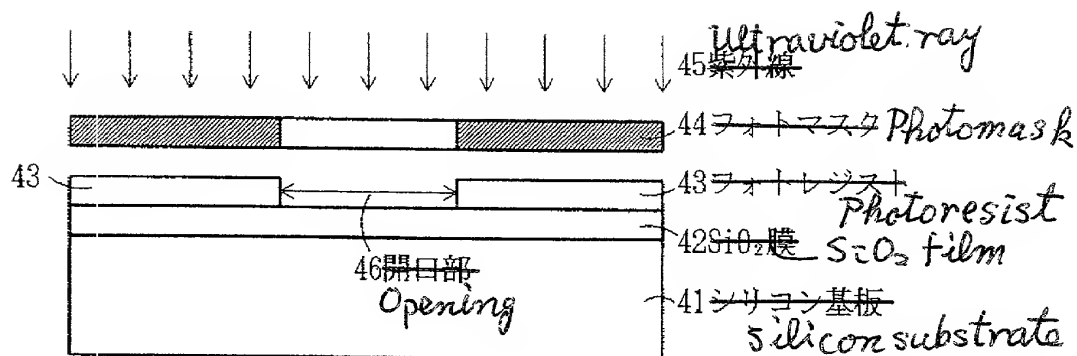


Fig. 16(b)

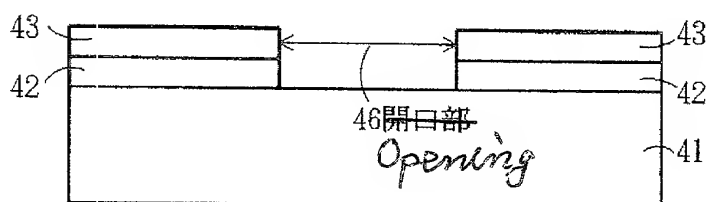


Fig. 16(c)

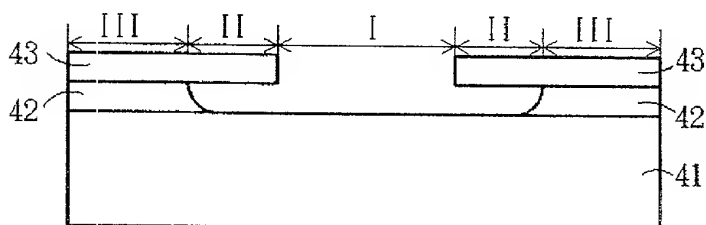


Fig. 16(d)

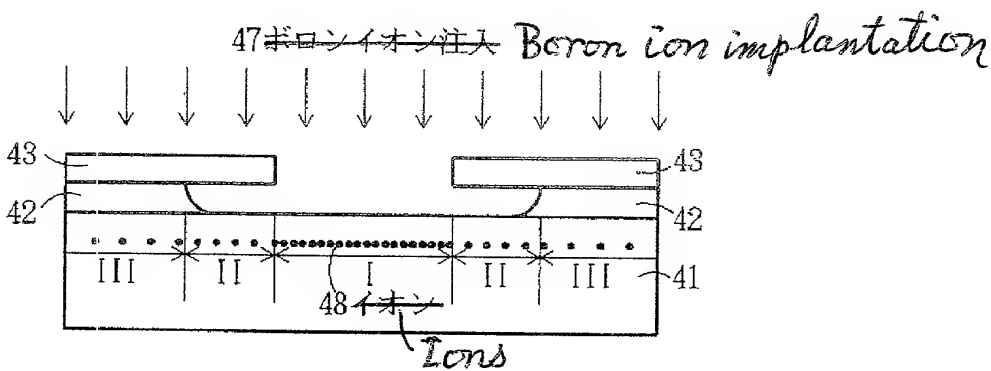
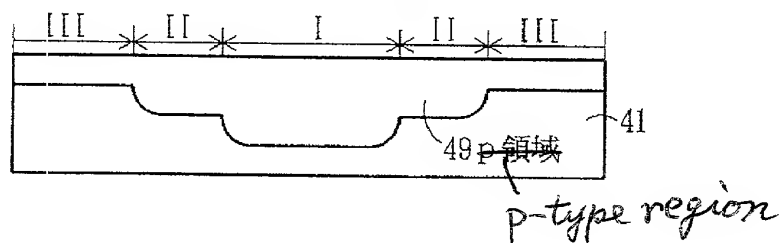
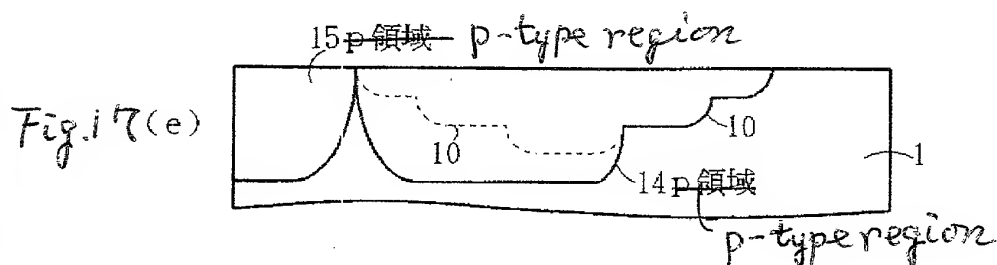
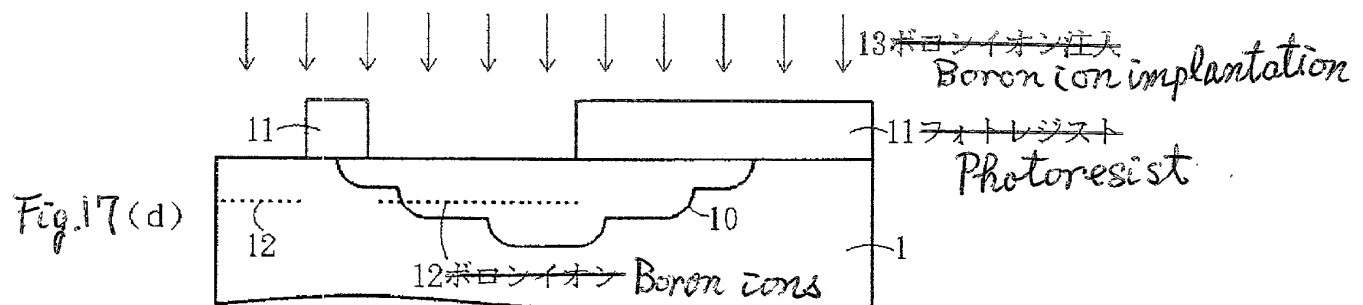
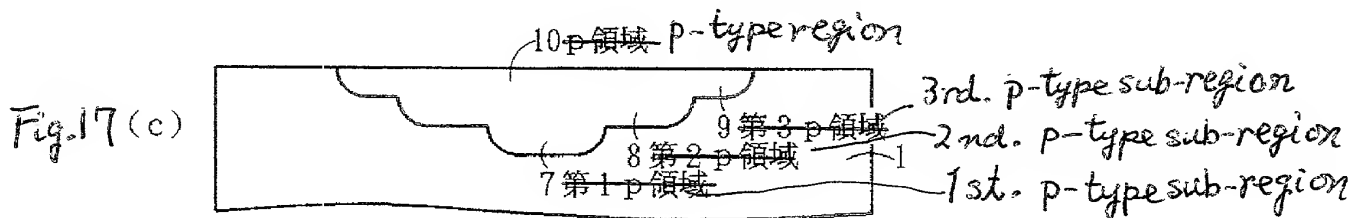
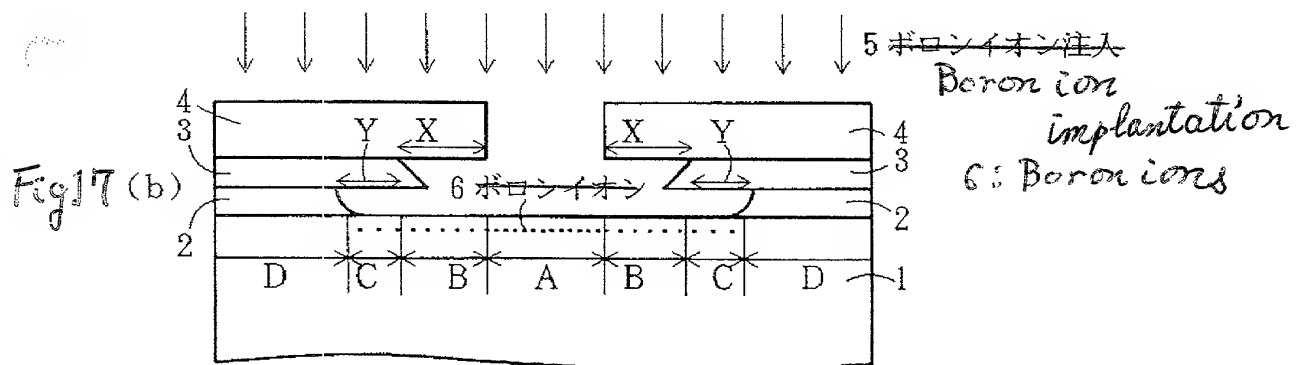
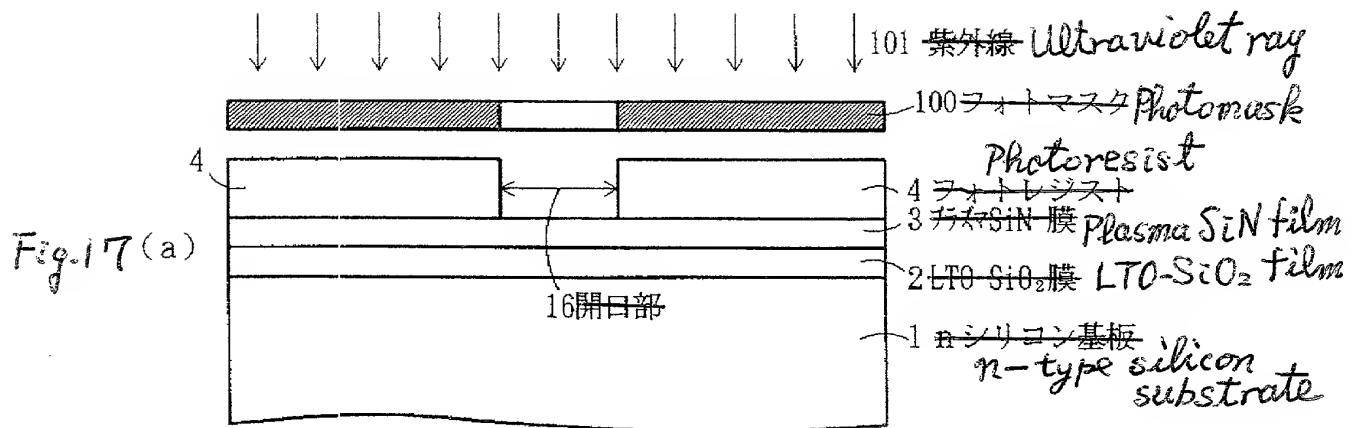
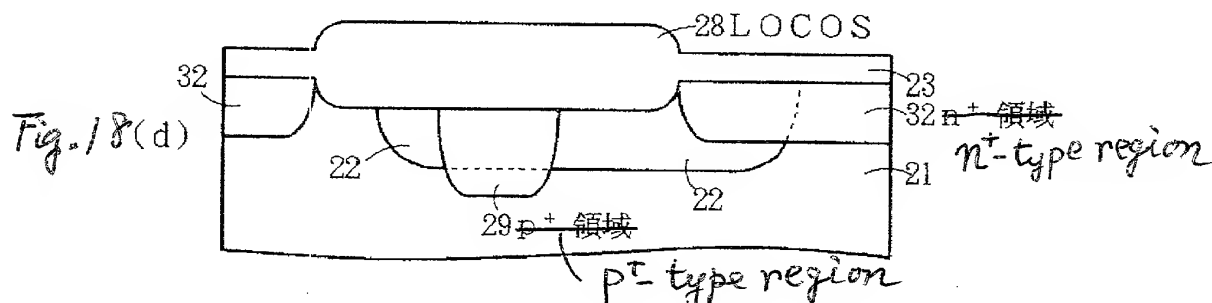
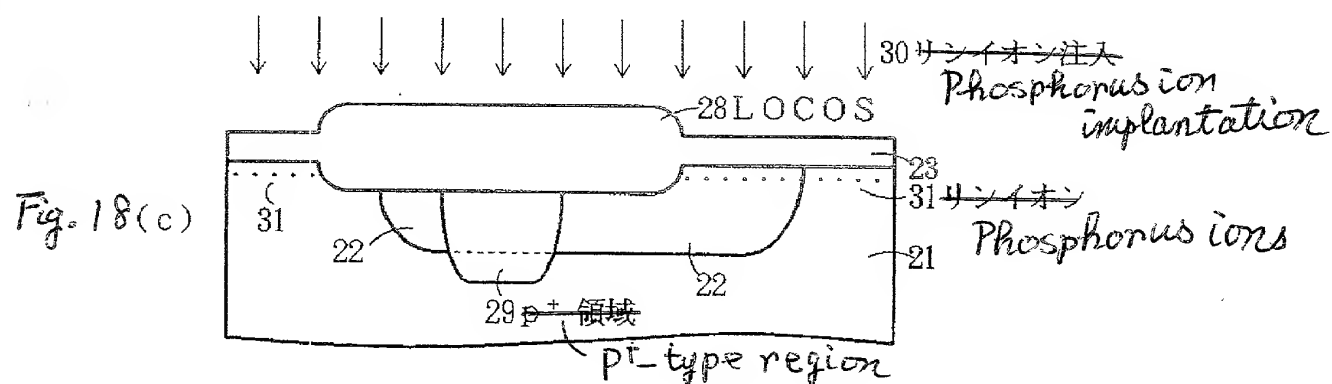
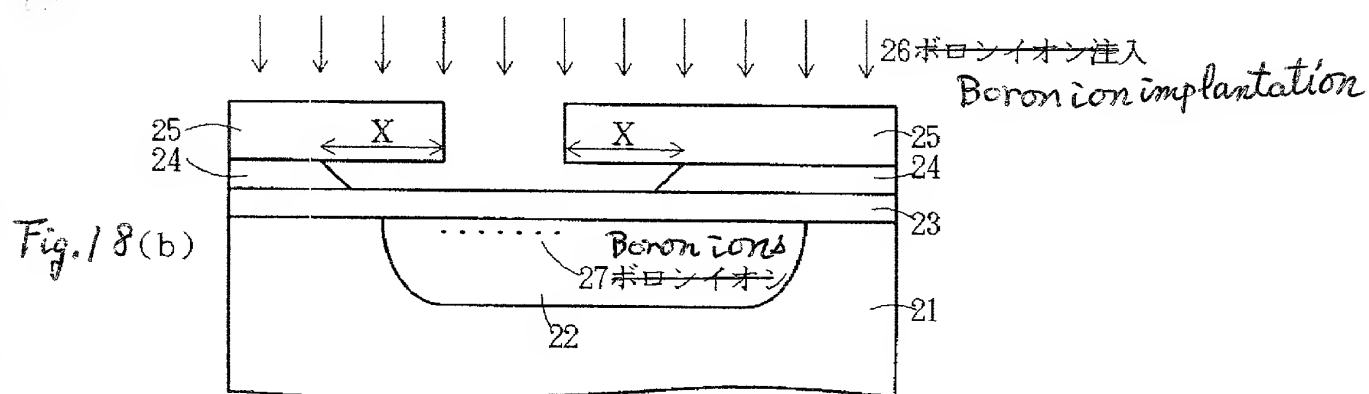
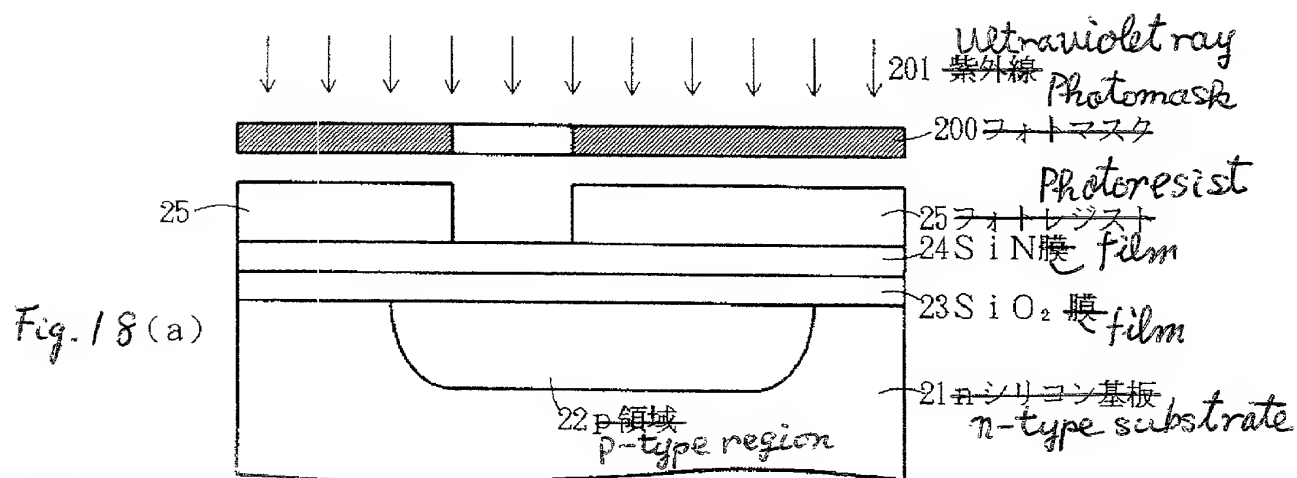


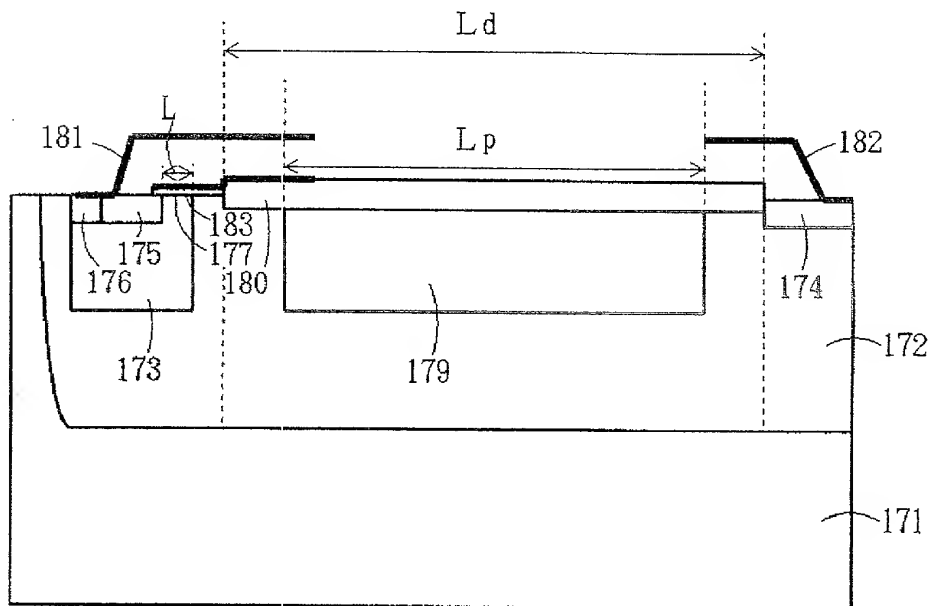
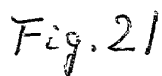
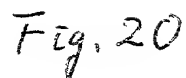
Fig. 16(e)











- |  |   |
|--|---|
| 171: p-type substrate                    | 177: Gate electrode                                 |
| 172: n-type well region                  | 179: p-type diffusion region (p-type offset region) |
| 173: p-type base region                  | 180: Insulation film                                |
| 174: n-type drain region                 | 181: Source electrode                               |
| 175: n-type source region                | 182: Drain electrode                                |
| 176: p <sup>+</sup> -type contact region | 183: Gate oxide film                                |

Fig. 22(a)

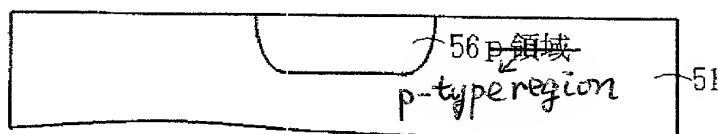
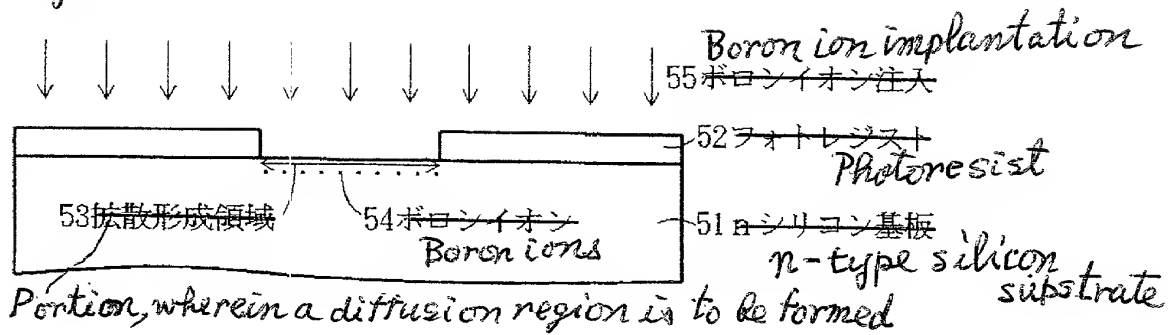


Fig. 22(b)

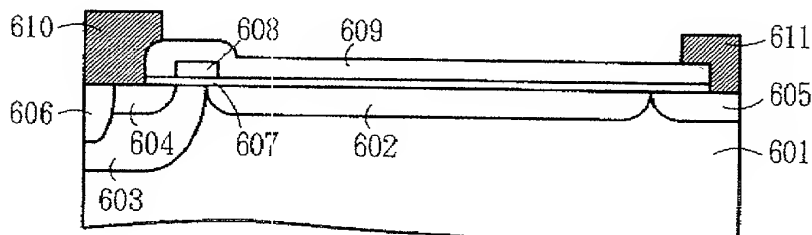


Fig. 23

- |   |                       |
|---|-----------------------|
| 601: n-type silicon substrate             | 607: Gate oxide film  |
| 602: p-type region (p-type offset region) | 608: Gate electrode   |
| 603: p-type region (p-type base region)   | 609: Insulation film  |
| 604: n-type source region                 | 610: Source electrode |
| 605: n-type drain region                  | 611: Drain electrode  |
| 606: p-type contact region                |                       |

Fig. 24

